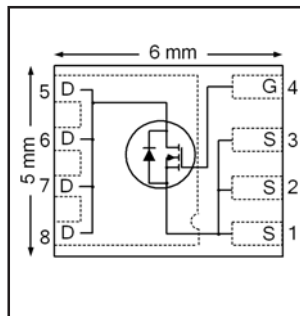


HEXFET® Power MOSFET

| | | |
|---|--------------|-----------|
| V_{DS} | 25 | V |
| $R_{DS(on) max}$ (@ $V_{GS} = 10V$) | 1.05 | mΩ |
| Q_g (typical) | 52 | nC |
| R_G (typical) | 1.3 | Ω |
| I_D (@ $T_{C(Bottom)} = 25°C$) | 100 ⑥ | A |



Applications

- OR-ing MOSFET for 12V (typical) Bus in-Rush Current
- Battery Operated DC Motor Inverter MOSFET

Features and Benefits

Features

| |
|--|
| Low RDSon (<1.05 mΩ) |
| Low Thermal Resistance to PCB (<0.8°C/W) |
| Low Profile (<0.9 mm) |
| Industry-Standard Pinout |
| Compatible with Existing Surface Mount Techniques |
| RoHS Compliant Containing no Lead, no Bromide and no Halogen |
| MSL1, Industrial Qualification |

results in
⇒

Benefits

| |
|-----------------------------------|
| Lower Conduction Losses |
| Enable better thermal dissipation |
| Increased Power Density |
| Multi-Vendor Compatibility |
| Easier Manufacturing |
| Environmentally Friendly |
| Increased Reliability |

| Base part number | Package Type | Standard Pack | | Orderable part number |
|------------------|----------------|---------------|----------|-----------------------|
| | | Form | Quantity | |
| IRFH8202PbF | PQFN 5mm x 6mm | Tape and Reel | 4000 | IRFH8202TRPbF |

Absolute Maximum Ratings

| | Parameter | Max. | Units |
|-------------------------------|--|--------------|-------|
| V_{GS} | Gate-to-Source Voltage | ± 20 | V |
| $I_D @ T_A = 25°C$ | Continuous Drain Current, $V_{GS} @ 10V$ | 47 | A |
| $I_D @ T_A = 70°C$ | Continuous Drain Current, $V_{GS} @ 10V$ | 30 | |
| $I_D @ T_{C(Bottom)} = 25°C$ | Continuous Drain Current, $V_{GS} @ 10V$ | 100 ⑥ | |
| $I_D @ T_{C(Bottom)} = 100°C$ | Continuous Drain Current, $V_{GS} @ 10V$ | 100 ⑥ | |
| I_{DM} | Pulsed Drain Current ① | 400 | W |
| $P_D @ T_A = 25°C$ | Power Dissipation ⑤ | 3.6 | |
| $P_D @ T_{C(Bottom)} = 25°C$ | Power Dissipation ⑤ | 160 | |
| | Linear Derating Factor ⑤ | 0.029 | W/°C |
| T_J | Operating Junction and | -55 to + 150 | °C |
| T_{STG} | Storage Temperature Range | | |

Notes ① through ⑥ are on page 9

Static @ T_J = 25°C (unless otherwise specified)

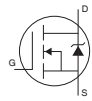
| | Parameter | Min. | Typ. | Max. | Units | Conditions |
|-------------------------------------|---|------|------|------|-------|--|
| BV _{DSS} | Drain-to-Source Breakdown Voltage | 25 | — | — | V | V _{GS} = 0V, I _D = 250μA |
| ΔBV _{DSS} /ΔT _J | Breakdown Voltage Temp. Coefficient | — | 0.02 | — | V/°C | Reference to 25°C, I _D = 1mA |
| R _{DS(on)} | Static Drain-to-Source On-Resistance | — | 0.90 | 1.05 | mΩ | V _{GS} = 10V, I _D = 50A ③ |
| | | — | 1.40 | 1.85 | | V _{GS} = 4.5V, I _D = 50A ③ |
| V _{GS(th)} | Gate Threshold Voltage | 1.35 | 1.80 | 2.35 | V | V _{DS} = V _{GS} , I _D = 150μA |
| ΔV _{GS(th)} | Gate Threshold Voltage Coefficient | — | -6.3 | — | mV/°C | |
| I _{DSS} | Drain-to-Source Leakage Current | — | — | 5.0 | μA | V _{DS} = 20V, V _{GS} = 0V |
| | | — | — | 150 | | V _{DS} = 20V, V _{GS} = 0V, T _J = 125°C |
| I _{GSS} | Gate-to-Source Forward Leakage | — | — | 100 | nA | V _{GS} = 20V |
| | Gate-to-Source Reverse Leakage | — | — | -100 | | V _{GS} = -20V |
| g _{fs} | Forward Transconductance | 181 | — | — | S | V _{DS} = 13V, I _D = 50A |
| Q _g | Total Gate Charge | — | 110 | — | nC | V _{GS} = 10V, V _{DS} = 13V, I _D = 50A |
| Q _g | Total Gate Charge | — | 52 | 78 | nC | V _{DS} = 13V V _{GS} = 4.5V I _D = 50A |
| Q _{gs1} | Pre-V _{th} Gate-to-Source Charge | — | 13 | — | | |
| Q _{gs2} | Post-V _{th} Gate-to-Source Charge | — | 7.8 | — | | |
| Q _{gd} | Gate-to-Drain Charge | — | 17 | — | | |
| Q _{godr} | Gate Charge Overdrive | — | 15 | — | | |
| Q _{sw} | Switch Charge (Q _{gs2} + Q _{gd}) | — | 25 | — | | |
| Q _{oss} | Output Charge | — | 36 | — | nC | V _{DS} = 16V, V _{GS} = 0V |
| R _G | Gate Resistance | — | 1.3 | 2.6 | Ω | |
| t _{d(on)} | Turn-On Delay Time | — | 28 | — | ns | V _{DD} = 13V, V _{GS} = 4.5V I _D = 50A R _G = 1.8Ω |
| t _r | Rise Time | — | 46 | — | | |
| t _{d(off)} | Turn-Off Delay Time | — | 30 | — | | |
| t _f | Fall Time | — | 19 | — | | |
| C _{iss} | Input Capacitance | — | 7174 | — | pF | V _{GS} = 0V V _{DS} = 13V f = 1.0MHz |
| C _{oss} | Output Capacitance | — | 1758 | — | | |
| C _{riss} | Reverse Transfer Capacitance | — | 828 | — | | |

Avalanche Characteristics

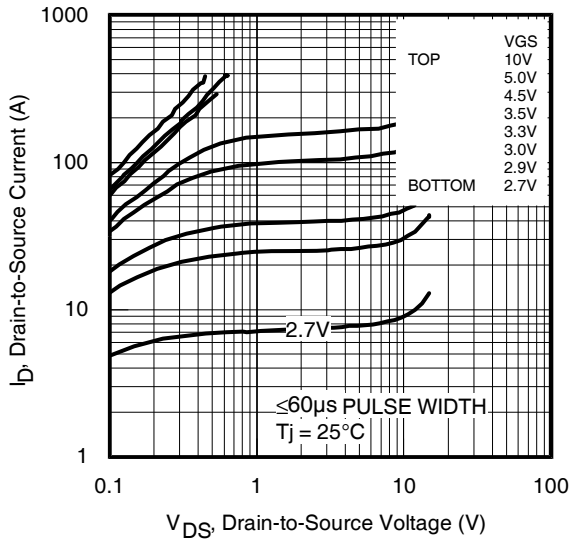
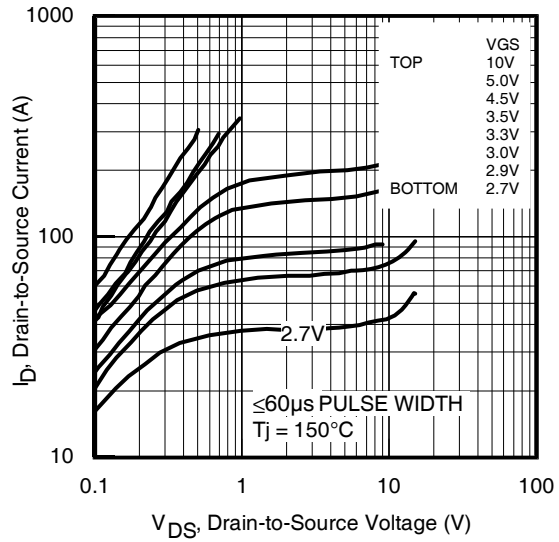
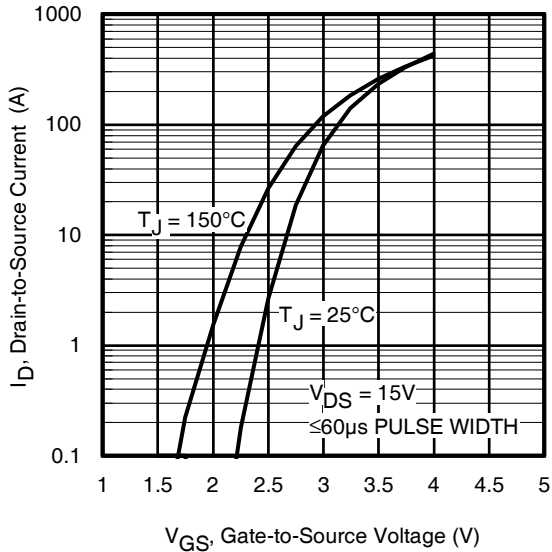
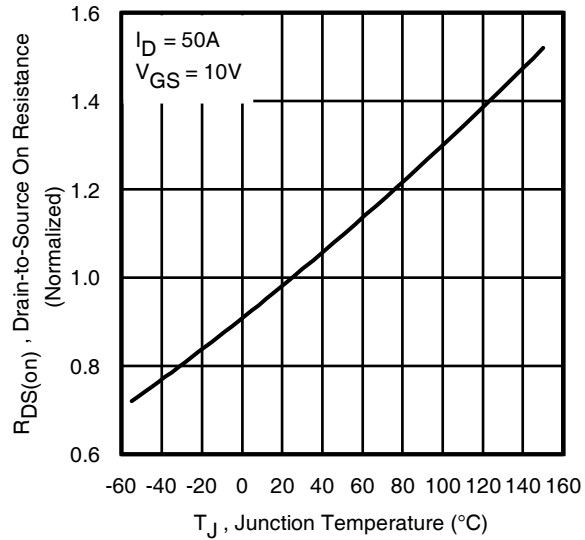
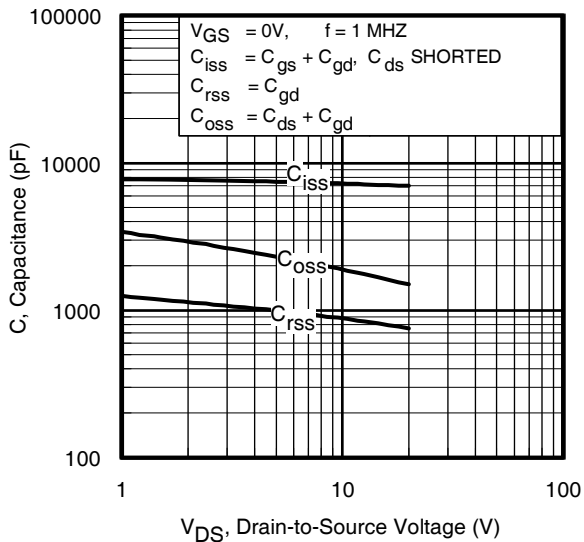
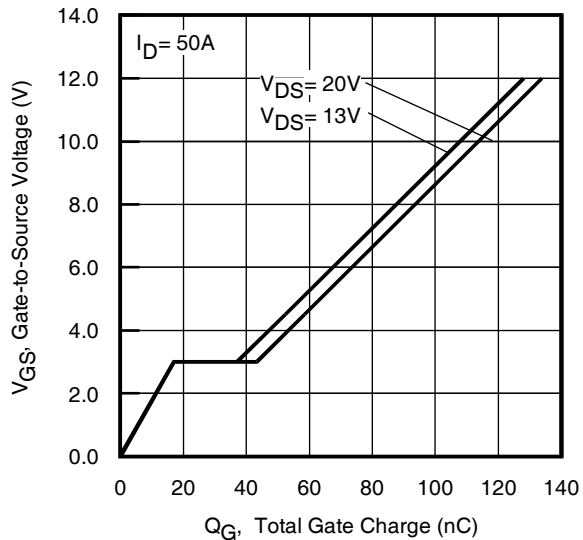
| | Parameter | Typ. | Max. | Units |
|-----------------|---------------------------------|------|------|-------|
| E _{AS} | Single Pulse Avalanche Energy ② | — | 468 | mJ |
| I _{AR} | Avalanche Current ① | — | 50 | A |

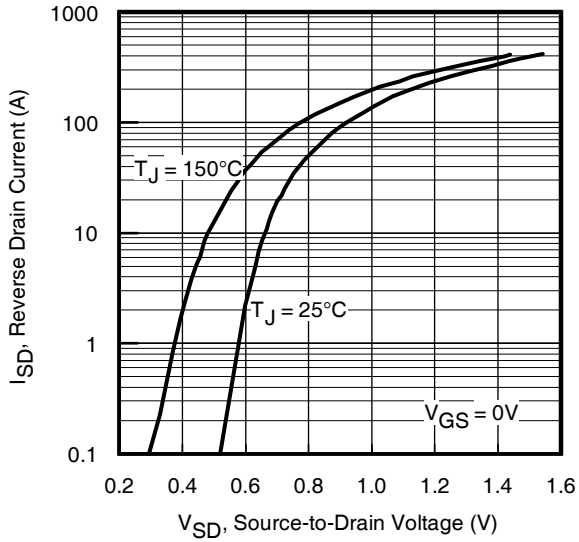
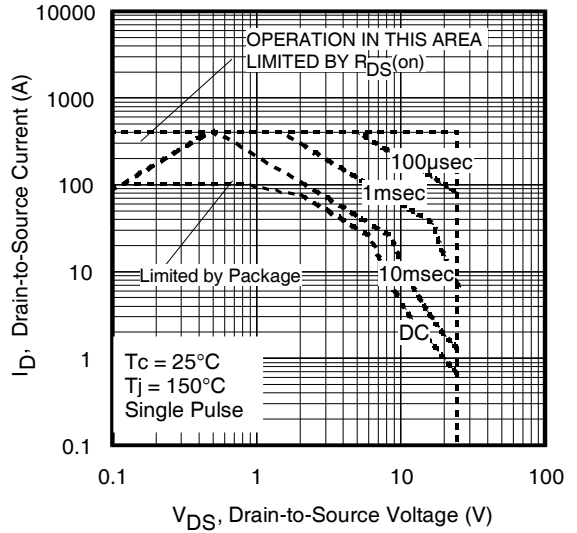
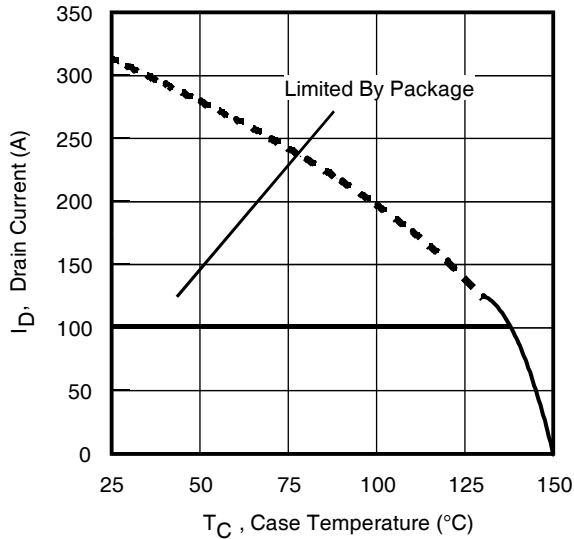
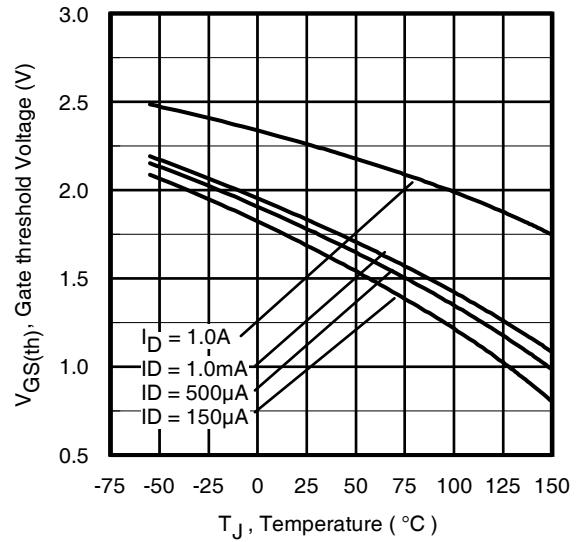
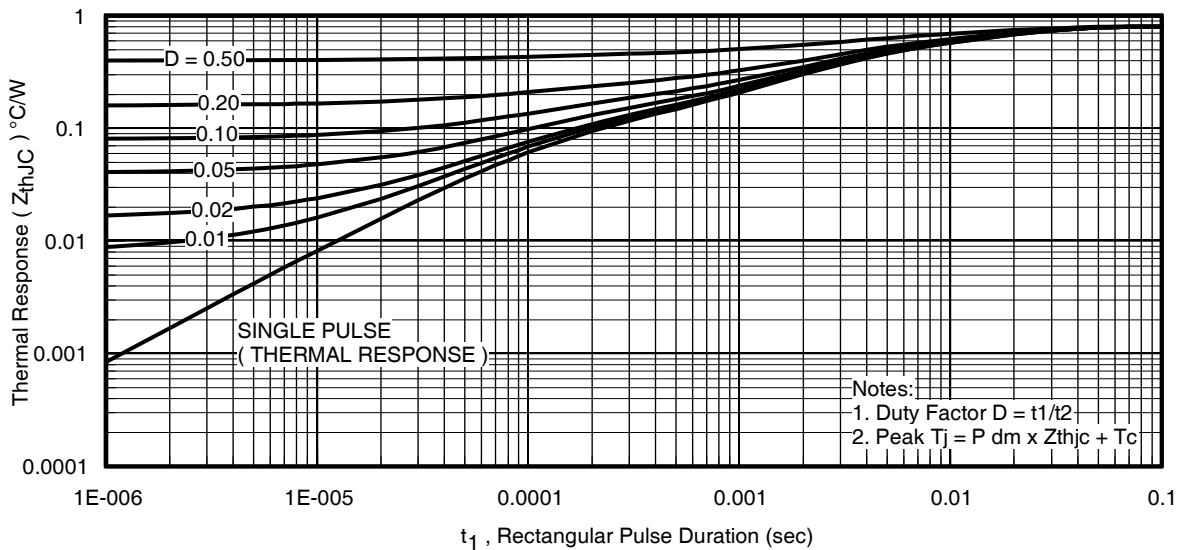
Diode Characteristics

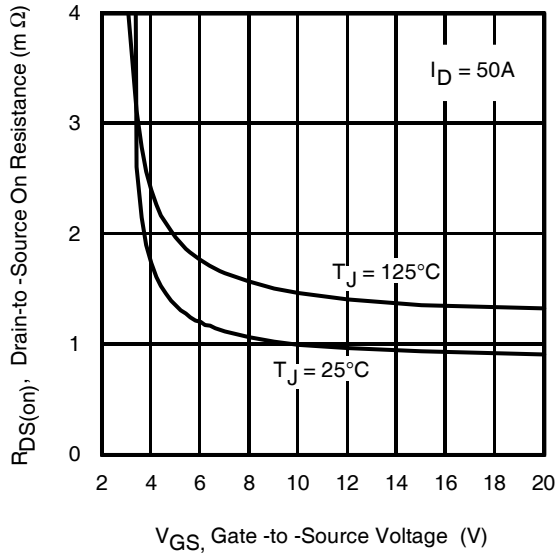
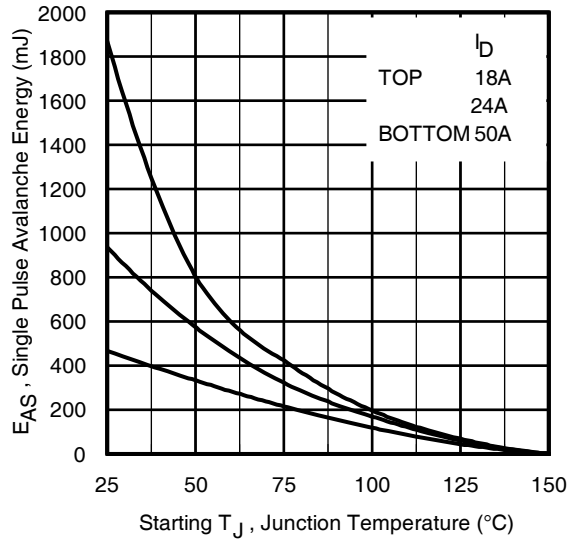
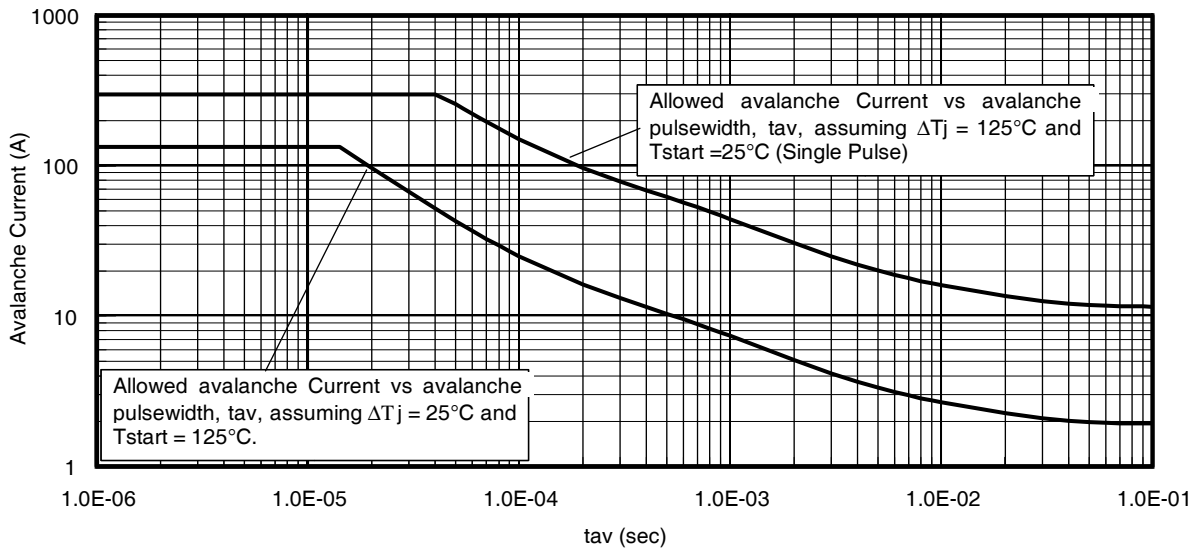
| | Parameter | Min. | Typ. | Max. | Units | Conditions |
|-----------------|---|------|------|-------|-------|---|
| I _S | Continuous Source Current (Body Diode) | — | — | 100 ⑥ | A | MOSFET symbol showing the integral reverse p-n junction diode. |
| I _{SM} | Pulsed Source Current (Body Diode) ① | — | — | 400 | | |
| V _{SD} | Diode Forward Voltage | — | — | 1.0 | V | T _J = 25°C, I _S = 50A, V _{GS} = 0V ③ |
| t _{rr} | Reverse Recovery Time | — | 37 | 56 | ns | T _J = 25°C, I _F = 50A, V _{DD} = 13V |
| Q _{rr} | Reverse Recovery Charge | — | 68 | 102 | nC | di/dt = 200A/μs ③ |

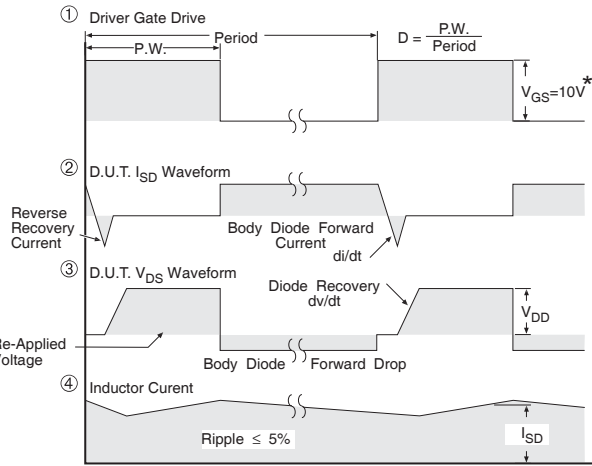
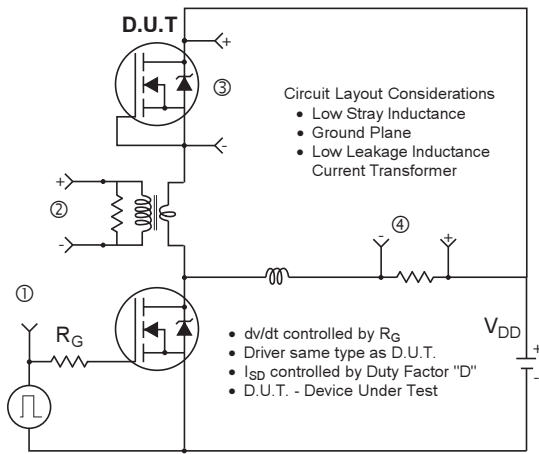

Thermal Resistance

| | Parameter | Typ. | Max. | Units |
|---------------------------|-----------------------|------|------|-------|
| R _{θJC} (Bottom) | Junction-to-Case ④ | 0.5 | 0.8 | °C/W |
| R _{θJC} (Top) | Junction-to-Case ④ | — | 15 | |
| R _{θJA} | Junction-to-Ambient ⑤ | — | 35 | |
| R _{θJA} (<10s) | Junction-to-Ambient ⑤ | — | 21 | |


Fig 1. Typical Output Characteristics

Fig 2. Typical Output Characteristics

Fig 3. Typical Transfer Characteristics

Fig 4. Normalized On-Resistance Vs. Temperature

Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage


Fig 7. Typical Source-Drain Diode Forward Voltage

Fig 8. Maximum Safe Operating Area

Fig 9. Maximum Drain Current Vs. Case (Bottom) Temperature

Fig 10. Threshold Voltage Vs. Temperature

Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case (Bottom)


Fig 12. On-Resistance vs. Gate Voltage

Fig 13. Maximum Avalanche Energy vs. Drain Current

Fig 14. Typical Avalanche Current vs. Pulsewidth



* $V_{GS} = 5V$ for Logic Level Devices

Fig 15. Peak Diode Recovery dv/dt Test Circuit for N-Channel HEXFET[®] Power MOSFETs

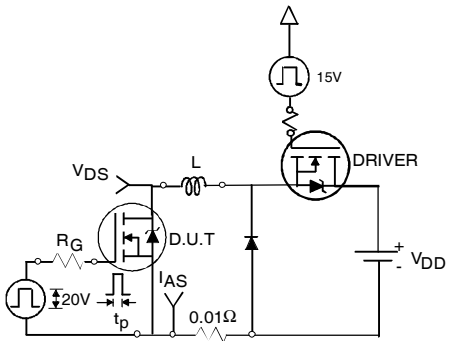


Fig 16a. Unclamped Inductive Test Circuit

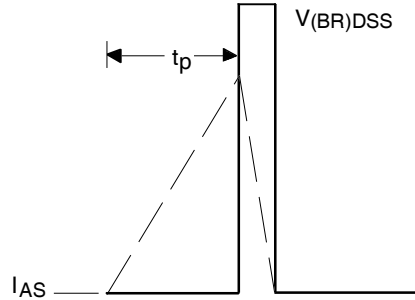


Fig 16b. Unclamped Inductive Waveforms

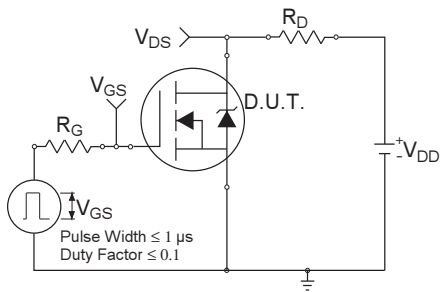


Fig 17a. Switching Time Test Circuit

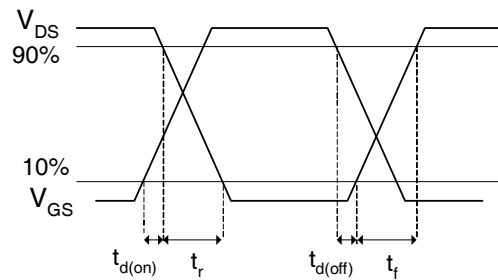


Fig 17b. Switching Time Waveforms

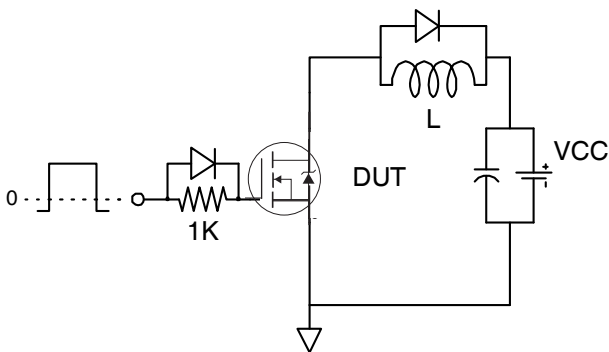


Fig 18a. Gate Charge Test Circuit

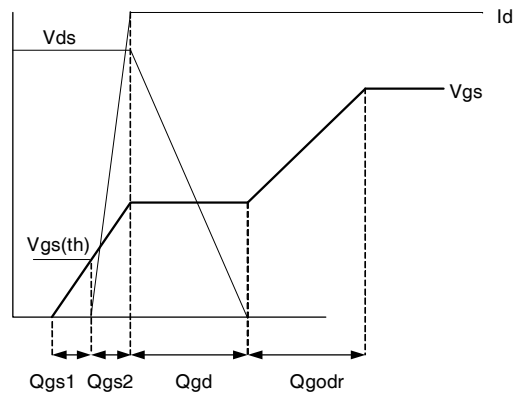
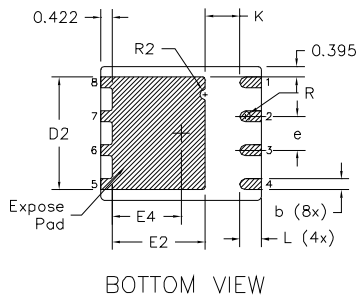
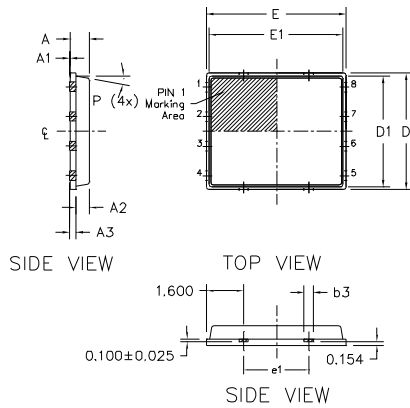


Fig 18b. Gate Charge Waveform

PQFN 5x6 Outline "B" Package Details

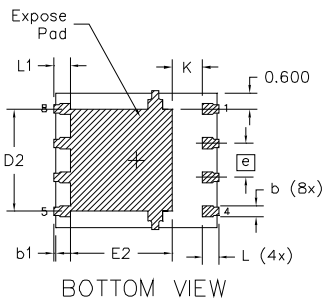
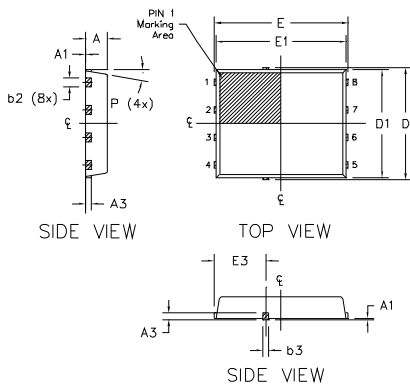


| DIM SYMBOL | MILLIMETERS | | INCH | |
|---------------|-------------|-------|------------|--------|
| | MIN | MAX | MIN | MAX |
| A | 0.800 | 0.900 | 0.0315 | 0.0543 |
| A1 | 0.000 | 0.050 | 0.0000 | 0.0020 |
| A3 | 0.200 REF | | 0.0079 REF | |
| b | 0.350 | 0.470 | 0.0138 | 0.0185 |
| b1 | 0.025 | 0.125 | 0.0010 | 0.0049 |
| b2 | 0.210 | 0.410 | 0.0083 | 0.0161 |
| b3 | 0.150 | 0.450 | 0.0059 | 0.0177 |
| D | 5.000 BSC | | 0.1969 BSC | |
| D1 | 4.750 BSC | | 0.1870 BSC | |
| D2 | 4.100 | 4.300 | 0.1614 | 0.1693 |
| E | 6.000 BSC | | 0.2362 BSC | |
| E1 | 5.750 BSC | | 0.2264 BSC | |
| E2 | 3.380 | 3.780 | 0.1331 | 0.1488 |
| e | 1.270 REF | | 0.0500 REF | |
| e1 | 2.800 REF | | 0.1102 REF | |
| K | 1.200 | 1.420 | 0.0472 | 0.0559 |
| L | 0.710 | 0.900 | 0.0280 | 0.0354 |
| P | 0° | 12° | 0° | 12° |
| R | 0.200 REF | | 0.0079 REF | |
| R2 | 0.150 | 0.200 | 0.0059 | 0.0079 |

Note:

1. Dimensions and tolerancing confirm to ASME Y14.5M-1994
2. Dimension L represents terminal full back from package edge up to 0.1mm is acceptable
3. Coplanarity applies to the expose Heat Slug as well as the terminal
4. Radius on terminal is Optional

PQFN 5x6 Outline "G" Package Details



| DIM SYMBOL | MILLIMETERS | | INCH | |
|---------------|-------------|--------|------------|--------|
| | MIN. | MAX. | MIN. | MAX. |
| A | 0.950 | 1.050 | 0.0374 | 0.0413 |
| A1 | 0.000 | 0.050 | 0.0000 | 0.0020 |
| A3 | 0.254 REF | | 0.0100 REF | |
| b | 0.310 | 0.510 | 0.0122 | 0.0201 |
| b1 | 0.025 | 0.125 | 0.0010 | 0.0049 |
| b2 | 0.210 | 0.410 | 0.0083 | 0.0161 |
| b3 | 0.180 | 0.450 | 0.0071 | 0.0177 |
| D | 5.150 BSC | | 0.2028 BSC | |
| D1 | 5.000 BSC | | 0.1969 BSC | |
| D2 | 3.700 | 3.900 | 0.1457 | 0.1535 |
| E | 6.150 BSC | | 0.2421 BSC | |
| E1 | 6.000 BSC | | 0.2362 BSC | |
| E2 | 3.560 | 3.760 | 0.1402 | 0.1488 |
| E3 | 2.270 | 2.470 | 0.0894 | 0.0972 |
| e | 1.27 REF | | 0.050 REF | |
| K | 0.830 | 1.400 | 0.0327 | 0.0551 |
| L | 0.510 | 0.710 | 0.0201 | 0.0280 |
| L1 | 0.510 | 0.710 | 0.0201 | 0.0280 |
| P | 10 deg | 12 deg | 0 deg | 12 deg |

Note:

1. Dimensions and tolerancing confirm to ASME Y14.5M-1994
2. Dimension L represents terminal full back from package edge up to 0.1mm is acceptable
3. Coplanarity applies to the expose Heat Slug as well as the terminal
4. Radius on terminal is Optional

For more information on board mounting, including footprint and stencil recommendation, please refer to application note AN-1136:

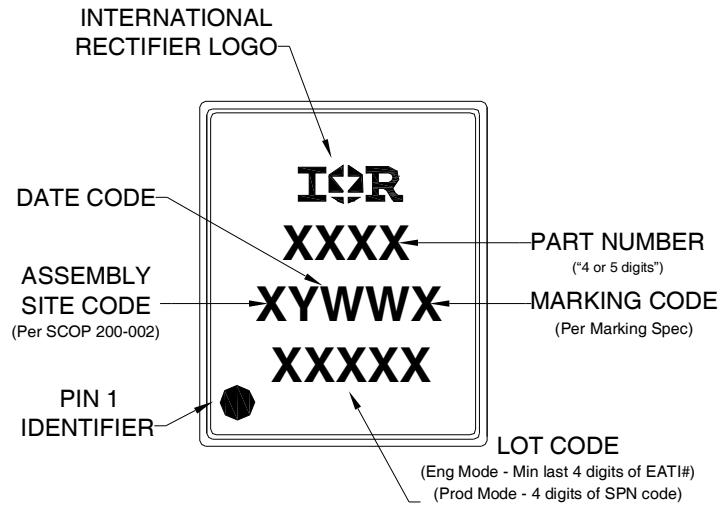
<http://www.irf.com/technical-info/appnotes/an-1136.pdf>

For more information on package inspection techniques, please refer to application note AN-1154:

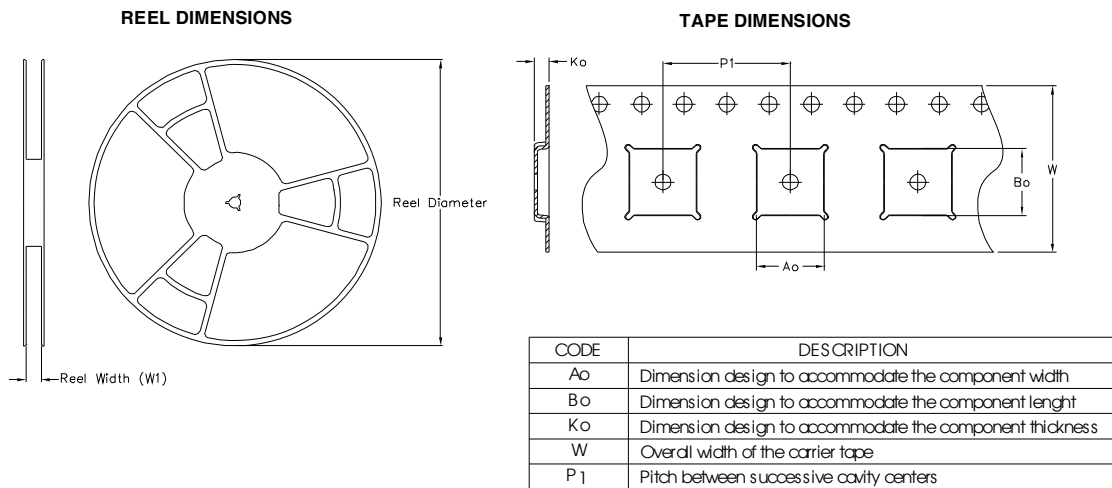
<http://www.irf.com/technical-info/appnotes/an-1154.pdf>

Note: For the most current drawing please refer to IR website at: <http://www.irf.com/package/>

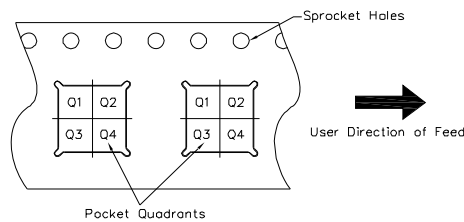
PQFN 5x6 Part Marking



PQFN 5x6 Tape and Reel



QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



Note: All dimension are nominal

| Package Type | Reel Diameter (Inch) | QTY | Reel Width W1 (mm) | Ao (mm) | Bo (mm) | Ko (mm) | P1 (mm) | W (mm) | Pin 1 Quadrant |
|--------------|----------------------|------|--------------------|---------|---------|---------|---------|--------|----------------|
| 5 X 6 PQFN | 13 | 4000 | 12.4 | 6.300 | 5.300 | 1.20 | 8.00 | 12 | Q1 |

Note: For the most current drawing please refer to IR website at: <http://www.irf.com/package/>

Qualification information[†]

| | | |
|----------------------------|---|---|
| Qualification level | Industrial (per JEDEC JESD47F guidelines) | |
| Moisture Sensitivity Level | PQFN 5mm x 6mm | MSL1 (per JEDEC J-STD-020D ^{††}) |
| RoHS compliant | Yes | |

† Qualification standards can be found at International Rectifier's web site
<http://www.irf.com/product-info/reliability>

†† Applicable version of JEDEC standard at the time of product release.

Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature.
- ② Starting $T_J = 25^\circ\text{C}$, $L = 0.37\text{mH}$, $R_G = 25\Omega$, $I_{AS} = 50\text{A}$.
- ③ Pulse width $\leq 400\mu\text{s}$; duty cycle $\leq 2\%$.
- ④ R_θ is measured at T_J of approximately 90°C .
- ⑤ When mounted on 1 inch square 2 oz copper pad on 1.5x1.5 in. board of FR-4 material.
<http://www.irf.com/technical-info/appnotes/an-994.pdf>
- ⑥ Calculated continuous current based on maximum allowable junction temperature. Package is limited to 100A by production test capability

Revision History

| Date | Comments |
|-----------|---|
| 8/1/2013 | • Added "Strong/RFET™" above part number on page 1 |
| 4/28/2015 | • Updated package outline for "option B" and added package outline for "option G" on page 7 • Updated tape and reel on page 8. |
| 5/19/2015 | • Updated package outline for "option G" on page 7. • Updated "IFX logo" on page 1 and page 9. |



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Электронная почта: sales@st-electron.ru

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Промышленная ул, дом № 19, литера Н,
помещение 100-Н Офис 331